

8A SiC Schottky Diode

Main Product Characteristics

| I _{F(AV)} | 8A, T _c =99°C | | | |
|--------------------------|--------------------------|--|--|--|
| V _{RRM} | 600V | | | |
| T, | 175°C | | | |
| V _{F(Typ)} 25°C | 1.45V | | | |

■ Features

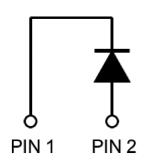
- Low Conduction and Switching Loss
- Positive Temperature Coefficient on V_F
- Temperature Independent Switching Behavior
- Fast Reverse Recovery
- High Surge Current Capability
- Pb-free lead plating

■ Benefits

- Higher System Efficiency
- Parallel Device Convenience
- High Temperature Application
- High Frequency Operation
- Hard Switching & High Reliability
- Environmental Protection

■ Outline





Package ITO-220AC

Inner Circuit

■ Applications

- SMPS
- PFC
- Solar/Wind Renewable Energy
- Power Inverters
- Motor Drives

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■ Maximum ratings and electrical characteristics

| Parameter | Conditions | Symbol | SIC08C60 | | UNIT | | |
|--|--|------------------|------------|------|------|------|--|
| Peak Repetitive Reverse Voltage | T _J =25°C | V _{RRM} | 600 | | | V | |
| Peak Reverse Surge Voltage | T _J =25°C | V _{RSM} | 600 600 | | | | |
| DC Blocking Voltage | T _J =25°C | V _R | | | | | |
| Continuous Forward Current | T _c =25°C | | 10.5 | | | A | |
| | T _c =80°C | I _F | | | | | |
| | T _c =135°C | | 4.5 | | | | |
| | T _c =25°C,T _p =10ms,Half Sine-Wave | | 64 | | | А | |
| Non-Repetitive Peak Forward surge current | T _c =125°C,T _p =10ms,Half Sine-Wave | I _{FSM} | | | | | |
| | T _c =25°C,T _p =10us,Pulse | 1 | 358 | | | | |
| | T _c =25°C,T _p =10ms,Half Sine-Wave,D=0.1 | | 50 | | | | |
| Repetitive Peak Forward surge current | T _c =125°C,T _p =10ms,Half Sine-Wave,D=0.1 | I _{FRM} | 41 | | | A | |
| | T _c =25°C | _ | 23.5 | | | W | |
| Power Dissipation | T _c =125°C | P _D | 7.5 | | | | |
| | | TJ | 175 | | | °C | |
| Operation Junction and Storage Temperature | | T _{stg} | -55 to 175 | | | | |
| Thermal Resistance Junction to Case | | R _{eJC} | 6.3 | | °C/W | | |
| Parameter | Conditions | Symbol | MIN. | TYP. | MAX. | UNIT | |
| DC Blocking Voltage | I _R =100uA,T _J =25°C | V _{DC} | | >650 | | V | |
| | I _F =8A,T _J =25°C | | | 1.45 | 1.8 | V | |
| Forward Voltage | I _F =8A,T _J =175°C | V _F | | 1.8 | 2.2 | | |
| | V _R =600V,T _J =25°C | | | <1 | 40 | uA | |
| Reverse Current | V _R =600V,T _J =175°C | I _R | | 12 | 160 | | |
| Total Capacitive Charge | I _F =8A,dI/dt=300A/us, V _R =400V,T _J =25°C | Q _c | 16 | | nC | | |
| | V _R =1V,T _J =25°C,f=1MHz | | | 301 | | | |
| Total Capacitive | V _R =200V,T _J =25°C,f=1MHz | С | | 48 | | pF | |
| | V _R =400V,T _J =25°C,f=1MHz | 1 | | 48 | | | |

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■ Rating and characteristic curves

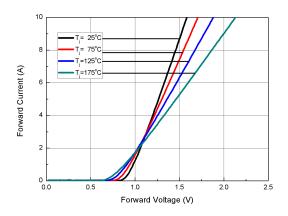


Fig. 1 Forward Characteristics

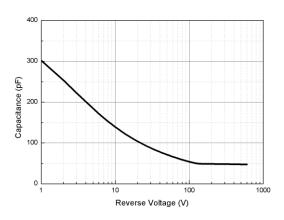


Fig. 3 Capacitance vs. Reverse Voltage

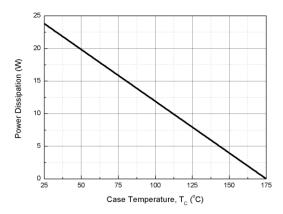


Fig. 5 Power Derating

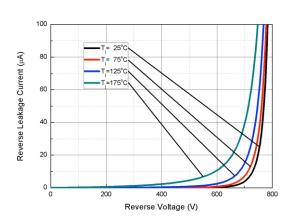


Fig. 2 Reverse Characteristics

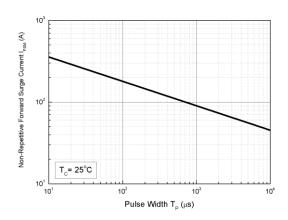


Fig. 4 Non-Repetitive Peak Forward Surge Current (Pulse Mode)

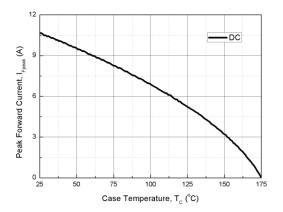


Fig. 6 Current Derating

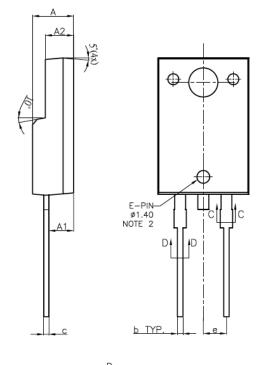
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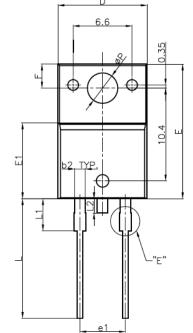


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■ Outline

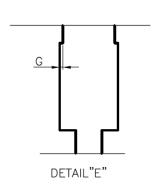


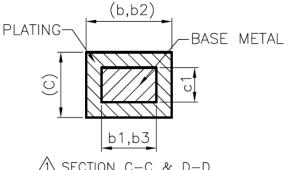
| | DIMENSIONS IN MILLIMETERS | | | | DIMENSIONS IN INCHES | | | |
|---------|---------------------------|----------|-------|--|----------------------|-----------|-------|--|
| SYMBOLS | MIN. | NOM. | MAX. | | MIN. | NOM. | MAX. | |
| А | 4.20 | 4.50 | 4.80 | | 0.165 | 0.177 | 0.189 | |
| A1 | 2.50 | | 2.90 | | 0.098 | | 0.114 | |
| A2 | 2.90 | 3.10 | 3.30 | | 0.114 | 0.122 | 0.130 | |
| b | 0.30 | | 0.93 | | 0.012 | | 0.037 | |
| b1 | 0.30 | 0.60 | 0.90 | | 0.012 | 0.024 | 0.035 | |
| b2 | 1.00 | | 1.43 | | 0.039 | | 0.056 | |
| b3 | 1.00 | 1.20 | 1.40 | | 0.039 | 0.047 | 0.055 | |
| С | 0.50 | | 0.73 | | 0.020 | | 0.029 | |
| c1 | 0.50 | 0.60 | 0.70 | | 0.020 | 0.024 | 0.028 | |
| D | 9.90 | 10.00 | 10.10 | | 0.390 | 0.394 | 0.398 | |
| E | 14.80 | 15.10 | 15.40 | | 0.583 | 0.594 | 0.606 | |
| E1 | 8.40 | 8.50 | 8.60 | | 0.331 | 0.335 | 0.339 | |
| е | | 2.55 BSC | | | | 0.100 BSC | | |
| e1 | | 5.10 BSC | | | | 0.200 BSC | | |
| F | 2.55 | 2.70 | 2.85 | | 0.100 | 0.106 | 0.112 | |
| G | 0.00 | | 0.127 | | 0.000 | | 0.005 | |
| L | 13.00 | 13.40 | 13.80 | | 0.512 | 0.528 | 0.543 | |
| L1 | 3.45 | 3.60 | 3.75 | | 0.136 | 0.142 | 0.148 | |
| L2 | | | 1.60 | | | | 0.063 | |
| ØΡ | 2.90 | 3.20 | 3.50 | | 0.114 | 0.126 | 0.138 | |



NOTES:

1.All dimension are in mm[inch]. 2.Tolerance: ±0.004inch.





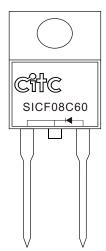
⚠ SECTION C-C & D-D

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■ Marking information



SICF08C60: Product type marking code

CTC Logo

■ Ordering/Packing infirmation

| | Part number | Case | Q'TY/Tube (PCS) | Q'TY Box(PCS) | Q'TY/Carton(PCS) |
|--------------|-------------|-----------|-----------------|---------------|------------------|
| Halogen Free | SICF08C60 | ITO-220AC | 50 | 4,000 | 8,000 |

Notes: 1. For packaging details, please reference our website at http://www.citcorp.com.tw/tchinese/products/index.php

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